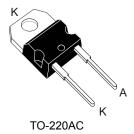


120 V power Schottky rectifier





Features

- High junction temperature capability
- Avalanche rated
- · Low leakage current
- Good trade-off between leakage current and forward voltage drop
- ECOPACK[®]2 compliant

Applications

- · Switching diode
- SMPS
- DC/DC converter
- LED lighting
- · Notebook adapter

Description

This single Schottky rectifier is suited for high frequency switch mode power supply.

Packaged in TO-220AC, the STPS20120D is optimized for use in notebook & LCD adaptors, desktop SMPS, providing in these applications a margin between the remaining voltages applied on the diode and the voltage capability of the diode.

Product status link				
STPS2	STPS20120D			
Product summary				
Symbol Value				
I _{F(AV)}	20 A			
V _{RRM}	120 V			
T _j (max.)	175 °C			
V_F (typ.) 0.72 V				



1 Characteristics

Table 1. Absolute ratings (limiting values at 25 °C unless otherwise specified)

Symbol	Parameter	Value	Unit	
V _{RRM}	Repetitive peak reverse voltage			V
I _{F(RMS)}	Forward rms current		30	А
I _{F(AV)}	Average forward current , δ = 0.5 square wave	20	А	
I _{FSM}	Surge non repetitive forward current $t_p = 10 \text{ ms sinusoidal}$		200	А
P _{ARM}	Repetitive peak avalanche power	619	W	
T _{stg}	Storage temperature range	-65 to +175	°C	
Tj	Maximum operating junction temperature (1)			°C

^{1.} $(dP_{tot}/dT_j) < (1/R_{th(j-a)})$ condition to avoid thermal runaway for a diode on its own heatsink.

Table 2. Thermal resistance parameters

Symbol	Parameter	Value	Unit
R _{th(j-c)}	Junction to case	2.2	°C/W

Table 3. Static electrical characteristics

Symbol	Parameter	Test conditions		Min.	Тур.	Max.	Unit
I _R ⁽¹⁾	1 (1)	T _j = 25 °C	V -V	-		20	μA
'R'	Reverse leakage current	T _j = 125 °C	$V_R = V_{RRM}$	-	3	10	mA
		T _j = 25 °C	I _F = 5 A	-		0.70	
		T _j = 125 °C		-	0.54	0.58	
V _F ⁽²⁾	Converd veltage drep	T _j = 25 °C		-		0.80	V
VF(=/	V _F ⁽²⁾ Forward voltage drop	T _j = 125 °C		-	0.62	0.66	V
		T _j = 25 °C	L = 20 A	-		0.93	
		T _j = 125 °C	I _F = 20 A	-	0.72	0.76	

^{1.} Pulse test: tp = 5 ms, $\delta < 2\%$

To evaluate the conduction losses, use the following equation:

 $P = 0.56 \times I_{F(AV)} + 0.010 \times I_{F}^{2}_{(RMS)}$

For more information, please refer to the following application notes related to the power losses :

- AN604: Calculation of conduction losses in a power rectifier
- AN4021: Calculation of reverse losses on a power diode

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^{2.} Pulse test: $t_p = 380 \ \mu s, \ \delta < 2\%$



1.1 Characteristics (curves)

Figure 1. Average forward power dissipation versus average forward current

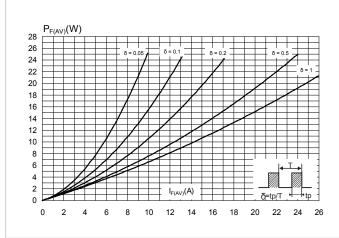


Figure 2. Average forward current versus ambient temperature (δ = 0.5)

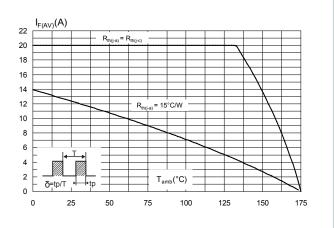


Figure 3. Normalized avalanche power derating versus pulse duration ($T_i = 125$ °C)

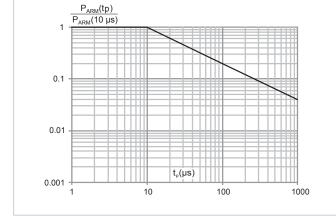
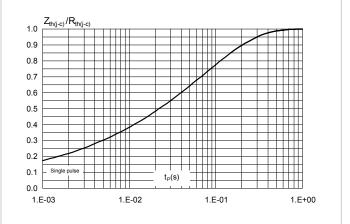


Figure 4. Relative variation of thermal impedance junction to case versus pulse duration



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1.E+02
1.E+01
1.E-01
1.E-02
1.E-03
1.E-04
1.E-05
0 10 20 30 40 50 60 70 80 90 100 110 120

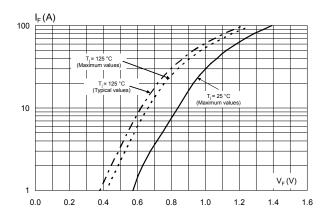
Figure 6. Junction capacitance versus reverse voltage applied (typical values)

1000 C(pF)

1000 V_R(V)

100 100 100

Figure 7. Forward voltage drop versus forward current



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Package information

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: www.st.com. ECOPACK® is an ST trademark.

2.1 TO-220AC package information

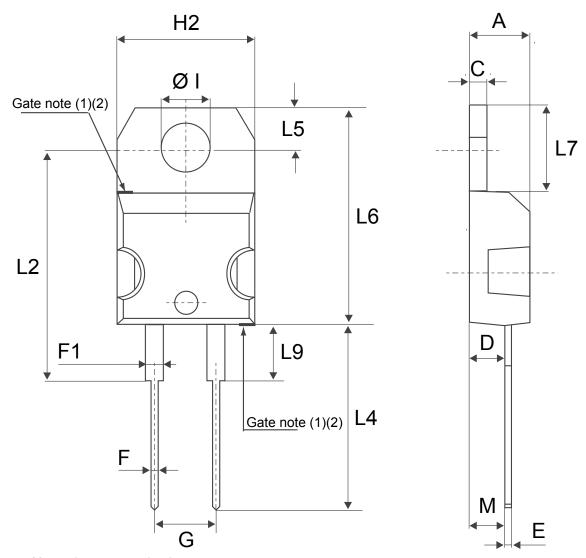
Epoxy meets UL 94,V0

Cooling method: by conduction (C)

Recommended torque value: 0.55 N·m

Maximum torque value: 0.70 N·m

Figure 8. TO-220AC package outline



- (1) :Max resin gate protusion 0.5 mm
- (2) :Resin gate position is accepted in each of the two positions shown on the drawings or their symmetrical

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Table 4. TO-220AC package mechanical data

	Dimensions				
Ref.	Millimeters		Inches (for reference only)		
	Min.	Max.	Min.	Max.	
Α	4.40	4.60	0.173	0.181	
С	1.23	1.32	0.048	0.051	
D	2.40	2.72	0.094	0.107	
E	0.49	0.70	0.019	0.027	
F	0.61	0.88	0.024	0.034	
F1	1.14	1.70	0.044	0.066	
G	4.95	5.15	0.194	0.202	
H2	10.00	10.40	0.393	0.409	
L2	16.40 typ.		0.645 typ.		
L4	13.00	14.00	0.511	0.551	
L5	2.65	2.95	0.104	0.116	
L6	15.25	15.75	0.600	0.620	
L7	6.20	6.60	0.244	0.259	
L9	3.50	3.93	0.137	0.154	
M	2.60 typ.		0.102	2 typ.	
Diam	3.75	3.85	0.147	0.151	

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3 Ordering information

Table 5. Ordering information

Order code	Marking	Package	Weight	Base qty.	Delivery mode
STPS20120D	STPS20120D	TO-220AC	1.86 g	50	Tube

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Revision history

Table 6. Document revision history

Date	Version	Changes
18-Feb-2005	1	First issue.
		Removed figure 4 and figure 5. Updated Figure 3. Normalized avalanche power derating versus pulse
02-Jul-2018	2	duration (T_j = 125 °C) and Table 1. Absolute ratings (limiting values at 25 °C unless otherwise specified).
		Minor text changes to improve readability.

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